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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/549,364	07/17/2006	Makoto Ishida	278285US0PCT	5533
OBLON, SPIVAK, MCCLELLAND MAIER & NEUSTADT, P.C. 1940 DUKE STREET			EXAMINER	
			QUINTO, KEVIN V	
ALEXANDRIA, VA 22314		ART UNIT	PAPER NUMBER	
			2826	
			NOTIFICATION DATE	DELIVERY MODE
			10/10/2008	ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

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	Application No.	Applicant(s)				
Office Action Commence	10/549,364	ISHIDA ET AL.				
Office Action Summary	Examiner	Art Unit				
	Kevin Quinto	2826				
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address				
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).						
Status						
1)⊠ Responsive to communication(s) filed on <u>17 Se</u>	eptember 2008.					
	action is non-final.					
<u>/</u>	/ 					
	closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims						
4)⊠ Claim(s) <u>6,7 and 12-15</u> is/are pending in the ap	pplication.					
4a) Of the above claim(s) is/are withdrawn from consideration.						
5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>6,7 and 12-15</u> is/are rejected.						
7) Claim(s) is/are objected to.						
8) Claim(s) are subject to restriction and/or	election requirement.					
Application Papers						
9)☐ The specification is objected to by the Examiner.						
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).						
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.						
Priority under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of:						
·—						
3. Copies of the certified copies of the priority documents have been received in Application No						
application from the International Bureau (PCT Rule 17.2(a)).						
* See the attached detailed Office action for a list of the certified copies not received.						
255 and diagonous dominated control definition of the dominate copies not received.						
Attacherant						
Attachment(s) 1) Notice of References Cited (RTO 992) 4) Unitodian Summery (RTO 413)						
1) Notice of References Cited (PTO-892) 4) Interview Summary (PTO-413) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) Paper No(s)/Mail Date						
3) Information Disclosure Statement(s) (PTO/SB/08) 5) Notice of Informal Patent Application						
Paper No(s)/Mail Date 6) Other:						

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DETAILED ACTION

Response to Arguments

1. Applicant's arguments filed August 18, 2008 have been fully considered but they are not persuasive. The declaration filed on August 18, 2008 under 37 CFR 1.131 has been considered but is ineffective to overcome the Sakashita et al. (United States Patent Application Publication No. US 2005/0040516 A1) reference. 37 C.F.R. 1.131 states, "The showing of facts shall be such, in character and weight, as to establish reduction to practice prior to the effective date of the reference, or conception of the invention prior to the effective date of the reference coupled with due diligence from prior to said date to a subsequent reduction to practice or to the filing of the application. Original exhibits of drawings or records, or photocopies thereof, must accompany and form part of the affidavit or declaration or their absence must be satisfactorily explained." The evidence submitted is insufficient to establish conception coupled with due diligence. The declaration can only be effective in antedating the reference if it makes a "showing of facts [that is] such, in character and weight, as to establish ... conception of the invention prior to the effective date of the reference coupled with due diligence from said date...to the filing of the application." 37 CFR 1.131. As to the date of the "filing of the application," the applicants are entitled to their foreign priority date. See 35 USC 119; In re Mulder and Weems, 219 USPQ 189,192-193 (Fed. Cir. 1983) ("Section 119 is a "patent-saving" provision for the benefit of applicants, and an applicant is entitled to rely on it as a constructive reduction to practice to overcome the

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date of a reference under Rule 131."). The applicant is required to show some form of diligence for the entire period from just prior to the effective date of the reference to the filing date. See, again, In re Mulder and Weems, 219 USPQ at 193 ("A liberal construction of the rule, which is clearly intended to benefit applicants, will permit applicants to show diligence from just prior to the date of the reference to their convention filing date, rather than all the way from their proven conception date, but liberality cannot be extended to the point of eliminating all proof of diligence, no matter how short the period to be covered."). The declaration with the program of a research report meeting at National University Corporation TOYOHASHI UNIVERSITY OF TECHNOLOGY and the summary of the presented report does not contain evidence regarding diligence. Therefore the rejections made in the Office action mailed on April 17, 2008 stand.

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Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. Claim 6 is rejected under 35 U.S.C. 103(a) as being unpatentable over Pohjonen et al. (USPN 6,242,843 B1) in view of Higuchi et al. (United States Patent Application Publication No. US 2005/0179342 A1) and further in view of Sakashita et al. (United States Patent Application Publication No. US 2005/0040516 A1).

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4. In reference to claim 6, Pohjonen et al. (USPN 6,242,843 B1, hereinafter referred to as the "Pohjonen" reference) discloses a similar structure. Figure 7 of Pohjonen illustrates an ultrasonic sensor with a film (130) on a semiconductor single crystal substrate (200). An electrically conductive thin film (110) is on the film (130). A ferroelectric thin film (100) is disposed on the thin film (110). An upper electrode (120) is disposed on the ferroelectric thin film (100). The semiconductor single crystal substrate (200) is subjected to a treatment for adjusting a resonant frequency and an ultrasonic wave to be detected. Pohjonen does not disclose the use of a single crystal platinum material for the thin film or electrode or the use of a highly oriented ferroelectric film. However the use of such a material is well known in the art. Higuchi et al. (United States Patent Application Publication No. US 2005/0179342 A1, hereinafter referred to as the "Higuchi" reference) discloses that the use of a single crystal platinum film as an electrode in a piezoelectric element is well known in the art (p. 1, paragraphs 2-3) since it leads to the benefit of a well oriented piezoelectric film, in this case the ferroelectric film, PZT. In view of Higuchi, it would therefore be obvious to use a single crystal platinum material for the electrically conductive thin film and a highly oriented ferroelectric film. Furthermore, the applicant is reminded in this regard that it has been held that a mere selection of known materials generally understood to be suitable to make a device, the selection of the particular material being on the basis of suitability for the intended use, would be entirely obvious. See In re Leshin 227 F.2d 197, 125 USPQ 416 (CCPA 1960) and also Sinclair & Carroll Co. v. Interchemical Corp., 325 U.S. 327, 65 USPQ 297 (1945). Therefore these limitations are not patentable over Pohjonen and

Higuchi. Pohjonen does not disclose the use of an epitaxially grown gamma Al₂O₃ film. However the use of this film is well known in the art. Sakashita et al. (United States Patent Application Publication No. US 2005/0040516 A1, hereinafter referred to as the "Sakashita" reference) discloses the use of an epitaxially grown gamma Al₂O₃ film in a ferroelectric structure in order to provide a barrier between the substrate and the electrode film so as prevent a reaction between them as well as to provide the base for orienting the electrode film (p. 4, paragraph 47 and p. 5, paragraph 54). In view of Sakashita, it would therefore be obvious to use an epitaxially grown gamma Al₂O₃ film. The examiner notes the limitation regarding the use of an epitaxial process to form the Pt thin film. However this places the claim into the form of a **product-by-process claim**:

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Note that a "product by process" claim is directed to the product per se, no matter how actually made, *In re Hirao*, 190 USPQ 15 at 17 (footnote 3). See also *In re Thorpe*, 227 USPQ 964, 966; *In re Luck*, 177 USPQ 523; *In re Fessmann*, 180 USPQ 324; *In re Avery*, 186 USPQ 161; *In re Wertheim*, 191 USPQ 90 (209 USPQ 554 does not deal with this issue); and *In re Marosi* et al., 218 USPQ 289, all of which make it clear that it is the patentability of the final product per se which must be determined in a "product by process" claim, and not the patentability of the process, and that an old or obvious product produced by a new method is not patentable as a product, whether claimed in " product by process" claims or not. Note that applicant has the burden of proof in such cases, as the above case law makes clear. See also MPEP 2113.

Claim 6 is not patentably distinguishable from the Pohjonen, Higuchi, and Sakashita references regardless of the process used to form the Pt thin film, because only the final product is relevant, and not the process of making such as epitaxial growth.

- 5. With regard to claim 12, the semiconductor single crystal is an Si single crystal (column 3, lines 46-48).
- 6. In reference to claim 14, Pohjonen discloses (column 3, lines 65-67, column 4, lines 1-4) the use of ZnO, PbTiO₃, and Pb_yLa_{1-y}Zr_xTi_{1-x}O₃.

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7. Claim 7 is rejected under 35 U.S.C. 103(a) as being unpatentable over Pohjonen et al. (USPN 6,242,843 B1) in view of Higuchi et al. (United States Patent Application Publication No. US 2005/0179342 A1) and further in view of Sakashita et al. (United States Patent Application Publication No. US 2005/0040516 A1) as applied to claim 6 above, and further in view Ziegler (USPN 6,238,946 B1).

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- 8. With regard to claim 7, Pohjonen does not disclose the use of an SOI substrate. However Ziegler (USPN 6,238,946 B1) discloses that the use of an SOI substrate for a resonator is well known in the art (column 5, lines 17-25). The applicant is reminded in this regard that it has been held that a mere selection of known materials generally understood to be suitable to make a device, the selection of the particular material being on the basis of suitability for the intended use, would be entirely obvious. See *In re Leshin* 227 F.2d 197, 125 USPQ 416 (CCPA 1960) and also *Sinclair & Carroll Co. v. Interchemical Corp.*, 325 U.S. 327, 65 USPQ 297 (1945). Therefore claim 7 is not patentable over Pohjonen and Ziegler.
- 9. Claim 15 is rejected under 35 U.S.C. 103(a) as being unpatentable over Pohjonen et al. (USPN 6,242,843 B1) in view of Higuchi et al. (United States Patent Application Publication No. US 2005/0179342 A1) and further in view of Sakashita et al. (United States Patent Application Publication No. US 2005/0040516 A1) as applied to claim 6 above, and further in view Tabata et al. (USPN 5,354,732).
- 10. With regard to claim 15, Pohjonen does not disclose the use of a gold black electrode. However Tabata et al. (USPN 5,354,732, hereinafter referred to as the "Tabata" reference) discloses that gold black is a known electrode material (column 1,

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lines 17-20). The applicant is reminded in this regard that it has been held that a mere selection of known materials generally understood to be suitable to make a device, the selection of the particular material being on the basis of suitability for the intended use, would be entirely obvious. See *In re Leshin* 227 F.2d 197, 125 USPQ 416 (CCPA 1960) and also *Sinclair & Carroll Co. v. Interchemical Corp.*, 325 U.S. 327, 65 USPQ 297 (1945). Therefore claim 15 is not patentable over Pohjonen and Tabata.

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- 11. Claim 13 is rejected under 35 U.S.C. 103(a) as being unpatentable over Pohjonen et al. (USPN 6,242,843 B1) in view of Higuchi et al. (United States Patent Application Publication No. US 2005/0179342 A1) and further in view of Sakashita et al. (United States Patent Application Publication No. US 2005/0040516 A1) as applied to claim 12 above, and further in view of Ando et al. (United States Patent Application Publication No. 2004/0021401 A1).
- 12. In reference to claim 13, Pohjonen does not disclose the use of a (100) face Si single crystal for the growth of the gamma Al₂O₃ film. However the use of a (100) face Si single crystal is well known in the art. Ando et al. (United States Patent Application Publication No. 2004/0021401 A1, hereinafter referred to as the "Ando" reference) discloses that a (100) face Si single crystal is easy to etch and therefore easy to process (p.3, paragraph 47). In view of Ando, it would therefore be obvious to use a (100) face Si single crystal.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Kevin Quinto whose telephone number is (571) 272-1920. The examiner can normally be reached on M-F 8AM-5PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Sue Purvis can be reached on (571) 272-1236. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Kevin Quinto/ Examiner, Art Unit 2826

/Evan Pert/ Primary Examiner, Art Unit 2826